



Small Signal Fast Switching Diodes



FEATURES

- Silicon epitaxial planar diode
- Electrically equivalent diodes: 1N4148 - 1N914
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
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APPLICATIONS

- Extreme fast switches

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MECHANICAL DATA

Case: DO-35 (DO-204AH)

Weight: approx. 105 mg

Cathode band color: black

Packaging codes / options:

TR/10K per 13" reel (52 mm tape), 50K/box

TAP/10K per ammpack (52 mm tape), 50K/box

PARTS TABLE				
PART	ORDERING CODE	TYPE MARKING	CIRCUIT CONFIGURATION	REMARKS
1N4148	1N4148-TAP or 1N4148TR	V4148	Single	Tape and reel / ammpack

ABSOLUTE MAXIMUM RATINGS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Repetitive peak reverse voltage		V_{RRM}	100	V
Reverse voltage		V_R	75	V
Peak forward surge current	$t_p = 1\text{ }\mu\text{s}$	I_{FSM}	2	A
Repetitive peak forward current		I_{FRM}	500	mA
Forward continuous current		I_F	300	mA
Average forward current	$V_R = 0$	$I_{F(AV)}$	150	mA
Power dissipation	$l = 4\text{ mm}, T_L = 45\text{ }^{\circ}\text{C}$	P_{tot}	440	mW
	$l = 4\text{ mm}, T_L \leq 25\text{ }^{\circ}\text{C}$	P_{tot}	500	mW

THERMAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Thermal resistance junction to ambient air	$l = 4\text{ mm}, T_L = \text{constant}$	R_{thJA}	350	K/W
Junction temperature		T_j	175	$^{\circ}\text{C}$
Storage temperature range		T_{stg}	-65 to +150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 10\text{ mA}$	V_F			1	V
Reverse current	$V_R = 20\text{ V}$	I_R			25	nA
	$V_R = 20\text{ V}, T_J = 150\text{ }^{\circ}\text{C}$	I_R			50	μA
Reverse current	$V_R = 75\text{ V}$	I_R			5	μA
	$I_R = 100\text{ }\mu\text{A}, t_p/T = 0.01,$ $t_p = 0.3\text{ ms}$	$V_{(BR)}$	100			V
Diode capacitance	$V_R = 0\text{ V}, f = 1\text{ MHz},$ $V_{HF} = 50\text{ mV}$	C_D			4	pF
Rectification efficiency	$V_{HF} = 2\text{ V}, f = 100\text{ MHz}$	η_r	45			%
Reverse recovery time	$I_F = I_R = 10\text{ mA},$ $i_R = 1\text{ mA}$	t_{rr}			8	ns
	$I_F = 10\text{ mA}, V_R = 6\text{ V},$ $i_R = 0.1 \times I_R, R_L = 100\text{ }\Omega$	t_{rr}			4	ns

TYPICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)


Fig. 1 - Forward Voltage vs. Junction Temperature

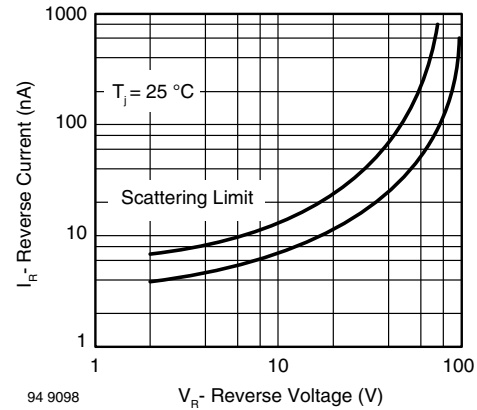


Fig. 3 - Reverse Current vs. Reverse Voltage



Fig. 2 - Forward Current vs. Forward Voltage



PACKAGE DIMENSIONS in millimeters (inches): **DO-35 (DO-204AH)**



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